



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Schuegraf et al.

Appl. No. : 08/932,228 ✓

Filed : September 17, 1997

For : SHALLOW TRENCH
ISOLATION USING LOW
DIELECTRIC CONSTANT
INSULATOR

Examiner : Hung Vu

) Group Art Unit 2811

) I hereby certify that this correspondence and all
) marked attachments are being deposited with
) the United States Postal Service as first-class
) mail in an envelope addressed to: Assistant
) Commissioner for Patents, Washington, D.C.
) 20231, on

August 29, 2000

(Date)

Adeel S. Akhtar, Reg. No. 41,394

AMENDMENT AND REQUEST FOR RECONSIDERATION

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In response to the Final Office Action mailed June 29, 2000, in the above-captioned application, Applicants respectfully request entry of the amendment below and reconsideration of the rejections in view of the remarks below.

IN THE CLAIMS:

11. (Twice Amended) An isolation structure in a semiconductor substrate comprising:
- a recessed portion formed [therein in] with a vertical sidewall within the semiconductor substrate; and
 - a dielectric material comprising a halide-doped silicon oxide filling the recessed portion, said dielectric material having a dielectric constant lower than the dielectric constant of silicon dioxide.